

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07793 D T-33-29

**2SD799**SILICON NPN TRIPLE DIFFUSED TYPE  
(DARLINGTON POWER)

IGNITER APPLICATIONS.

HIGH VOLTAGE SWITCHING APPLICATIONS.

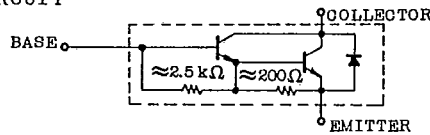
FEATURES:

- High DC Current Gain :  $h_{FE}=600(\text{Min.})(V_{CE}=2V, I_C=2A)$
- Monolithic Construction with Built-In Base-Emitter Shunt Resistor.

MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )

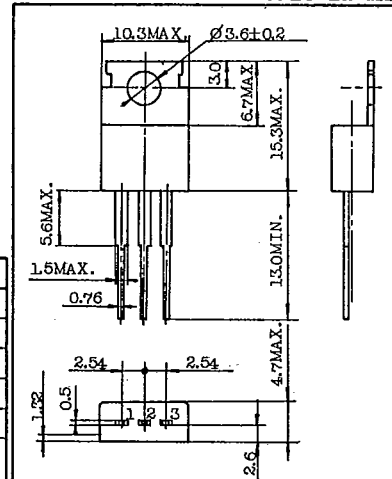
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	600	V
Collector-Emitter Voltage	$V_{CEO}$	400	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	6	A
Base Current	$I_B$	1	A
Collector Power Dissipation ( $T_c=25^\circ\text{C}$ )	$P_C$	30	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ\text{C}$

EQUIVALENT CIRCUIT



INDUSTRIAL APPLICATIONS

Unit in mm



1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC	TO - 220 AB
EIAJ	SC - 46
TOSHIBA	2 - 10A 1A

Mounting Kit No. AC75

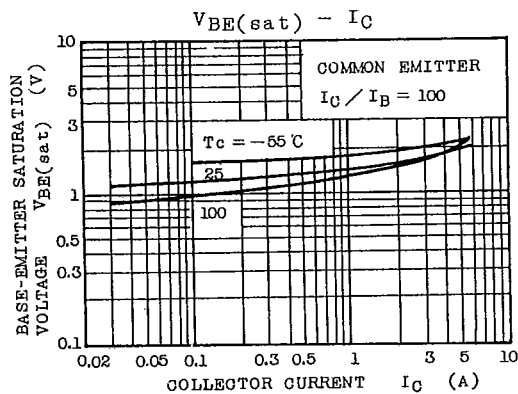
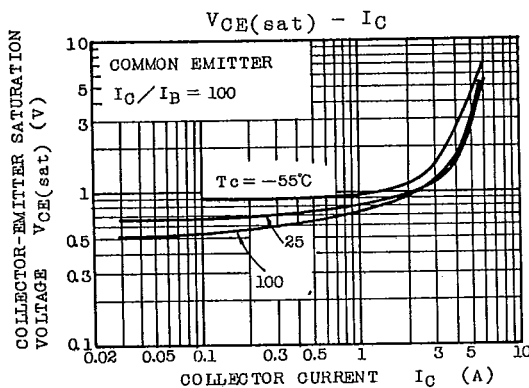
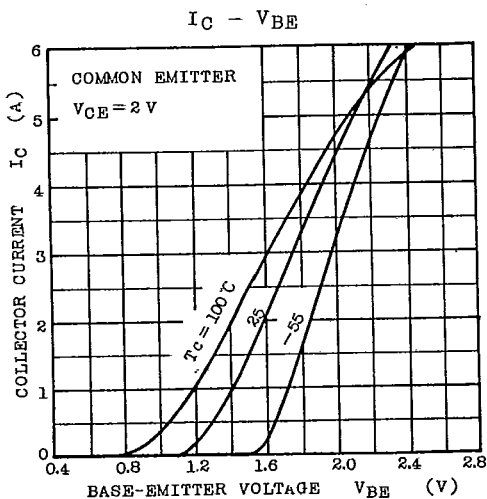
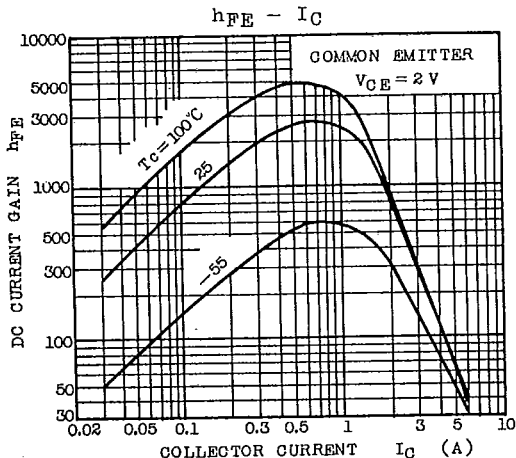
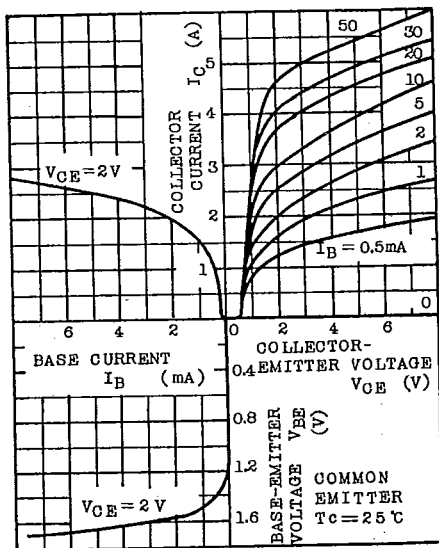
Weight : 1.9g

ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ )

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		$I_{CBO}$	$V_{CB}=600V, I_E=0$	-	-	0.5	mA
Emitter Cut-off Current		$I_{EBO}$	$V_{EB}=5V, I_C=0$	-	-	3	mA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	400	-	-	V
DC Current Gain		$h_{FE(1)}$	$V_{CE}=2V, I_C=2A$	600	-	-	
		$h_{FE(2)}$	$V_{CE}=2V, I_C=4A$	100	-	-	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=4A, I_B=0.04A$	-	-	2.0	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C=4A, I_B=0.04A$	-	-	2.5	V
Emitter-Collector Forward Voltage		$V_{ECF}$	$I_E=4A, I_B=0$	-	-	3.0	V
Collector Output Capacitance		$C_{ob}$	$V_{CB}=50V, I_E=0, f=1MHz$	-	35	-	pF
Switching Time	Turn-on Time	$t_{on}$		-	1	-	$\mu\text{s}$
	Storage Time	$t_{stg}$		-	8	-	
	Fall Time	$t_f$		-	-	5	

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STATIC CHARACTERISTICS



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**2SD799**

